

ABSTRACT OF THE DISCLOSURE

Provided are an etching method which uses an additive gas
stably suppliable also in future, is reduced in the problem of
5 particle contamination, is free from the problem of removability
of side-wall protection film and has high shape controlling
capacity, and a manufacturing method a highly-reliable
semiconductor device by using this etching method. This etching
method comprises depositing metal film including an aluminum
10 over a semiconductor device and etching the metal film with a
plasma of a mixture gas containing a Cl₂ gas, a BC_l₃ gas and a
CH₂Cl₂ gas.

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